

Hong Chen

List of Publications by Year in descending order

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52
papers

922
citations

516710

16
h-index

454955

30
g-index

55
all docs

55
docs citations

55
times ranked

1185
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature-dependent photoluminescence in light-emitting diodes. Scientific Reports, 2014, 4, 6131.	3.3	122
2	Realization of high-luminous-efficiency InGaN light-emitting diodes in the "green gap" range. Scientific Reports, 2015, 5, 10883.	3.3	96
3	Polarization Coulomb field scattering in AlGaN/AlN/GaN heterostructure field-effect transistors. Applied Physics Letters, 2011, 98, .	3.3	77
4	Investigation of temperature-dependent photoluminescence in multi-quantum wells. Scientific Reports, 2015, 5, 12718.	3.3	67
5	Piezo-Phototronic Effect in a Quantum Well Structure. ACS Nano, 2016, 10, 5145-5152.	14.6	63
6	Extraction of AlGaN/GaN heterostructure Schottky diode barrier heights from forward current-voltage characteristics. Journal of Applied Physics, 2011, 109, .	2.5	59
7	A novel wavelength-adjusting method in InGaN-based light-emitting diodes. Scientific Reports, 2013, 3, 3389.	3.3	56
8	Influence of the side-Ohmic contact processing on the polarization Coulomb field scattering in AlGaN/AlN/GaN heterostructure field-effect transistors. Applied Physics Letters, 2012, 101, .	3.3	39
9	Piezo-Phototronic Effect Controlled Dual-Channel Visible light Communication (PVLC) Using InGaN/GaN Multiquantum Well Nanopillars. Small, 2015, 11, 6071-6077.	10.0	38
10	Defect effect on the performance of nonpolar GaN-based ultraviolet photodetectors. Applied Physics Letters, 2021, 118, .	3.3	37
11	Evaluating AlGaN/AlN/GaN heterostructure Schottky barrier heights with flat-band voltage from forward current-voltage characteristics. Applied Physics Letters, 2011, 99, .	3.3	28
12	The enhanced photo absorption and carrier transportation of InGaN/GaN Quantum Wells for photodiode detector applications. Scientific Reports, 2017, 7, 43357.	3.3	28
13	Crystallographic and microstructural studies of BaTiO ₃ thin films grown on SrTiO ₃ by laser molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 275-278.	2.1	23
14	Indium segregation measured in InGaN quantum well layer. Scientific Reports, 2015, 4, 6734.	3.3	18
15	Threading dislocation density comparison between GaN grown on the patterned and conventional sapphire substrate by high resolution X-ray diffraction. Science China: Physics, Mechanics and Astronomy, 2010, 53, 465-468.	5.1	17
16	Improved optical and electrical performances of GaN-based light emitting diodes with nano truncated cone SiO ₂ passivation layer. Optical and Quantum Electronics, 2016, 48, 1.	3.3	17
17	Visualizing carrier transitions between localization states in a InGaN yellow "green light-emitting-diode structure. Journal of Applied Physics, 2019, 126, .	2.5	14
18	High performance visible-SWIR flexible photodetector based on large-area InGaAs/InP PIN structure. Scientific Reports, 2022, 12, 7681.	3.3	14

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19	Improvement of light power and efficiency droop in GaN-based LEDs using graded InGaN hole reservoir layer. Applied Physics A: Materials Science and Processing, 2014, 114, 1055-1059.	2.3	8
20	Improved crystal quality of non-polar a-plane GaN epi-layers directly grown on optimized hole-array patterned r-sapphire substrates. CrystEngComm, 2019, 21, 2747-2753.	2.6	8
21	Recent progress of GaN growth on maskless chemical-etched grooved sapphire substrate. Energy and Environmental Science, 2011, 4, 2625.	30.8	7
22	Fabrication of large-area nano-scale patterned sapphire substrate with laser interference lithography. Optoelectronics Letters, 2014, 10, 51-54.	0.8	7
23	Characterization of periodicity fluctuations in InGaN/GaN MQWs by the kinematical simulation of X-ray diffraction. Applied Physics Express, 2019, 12, 045502.	2.4	7
24	Characterization of different-Al-content AlGaIn/GaN heterostructures on sapphire. Science China: Physics, Mechanics and Astronomy, 2010, 53, 49-53.	5.1	5
25	Micro-Raman spectroscopy observation of field-induced strain relaxation in AlGaIn/GaN heterojunction field-effect transistors. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1174-1178.	1.8	5
26	Effect of Stair-Case Electron Blocking Layer on the Performance of Blue InGaIn Based LEDs. Journal of Display Technology, 2014, 10, 146-150.	1.2	5
27	A study of 2DEG properties in AlGaIn/GaN heterostructure using GaN/AlN superlattice as barrier layers grown by MOCVD. Applied Physics A: Materials Science and Processing, 2015, 118, 1453-1457.	2.3	5
28	Luminescence study in InGaAs/AlGaAs multi-quantum-well light emitting diode with p-n junction engineering. Journal of Applied Physics, 2020, 127, 085706.	2.5	5
29	Influence of the channel electric field distribution on the polarization Coulomb field scattering in AlGaIn/AlN/GaN heterostructure field-effect transistors. AIP Advances, 2013, 3, 092115.	1.3	4
30	Investigations of atomic configurations of 60° basal dislocations in wurtzite GaN film by high-resolution transmission electron microscopy. Philosophical Magazine Letters, 2016, 96, 148-156.	1.2	4
31	A method to extend wavelength into middle-wavelength infrared based on InAsSb/(Al)GaSb interband transition quantum well infrared photodetector*. Chinese Physics B, 2020, 29, 038504.	1.4	4
32	Effect of Mg and C contents in MgCNi ₃ , and structure and superconductivity of MgCNi _{3-x} -Co _x . Science in China Series A: Mathematics, 2001, 44, 1205-1208.	0.5	3
33	Temperature dependence of photoluminescence from self-organized Ge quantum dots with large size and low density. Science China: Physics, Mechanics and Astronomy, 2011, 54, 245-248.	5.1	3
34	Improvement on InGaIn-based light emitting diodes using p-GaN layer grown at low temperature in full N ₂ environment. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1175-1178.	1.8	3
35	Fabrication of metal nano-wires by laser interference lithography using a tri-layer resist process. Optical and Quantum Electronics, 2016, 48, 1.	3.3	3
36	Effect of SU-8 Passivation Layer Induced Stress on the Performance of GaSb Diode. IEEE Photonics Technology Letters, 2018, 30, 1060-1063.	2.5	3

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37	Experimental observation of isotropic in-plane spin splitting in GaN ^x AlGa _{1-x} N two-dimensional electron gas. Applied Physics Letters, 2007, 91, 252105.	3.3	2
38	The impact of nanoporous SiN _x interlayer growth position on high-quality GaN epitaxial films. Science Bulletin, 2011, 56, 2739-2743.	1.7	2
39	Suppressing the spread length of threading dislocations in AlSb/GaSb superlattice grown on (001) InP substrate. Applied Physics A: Materials Science and Processing, 2014, 115, 1239-1243.	2.3	2
40	Improvement in the crystal quality of non-polar a-plane GaN directly grown on an SiO ₂ stripe-patterned r-plane sapphire substrate. CrystEngComm, 2019, 21, 5124-5128.	2.6	2
41	N-polar GaN Film Epitaxy on Sapphire Substrate without Intentional Nitridation. Materials, 2022, 15, 3005.	2.9	2
42	Recent progress in single chip white light-emitting diodes with the InGa _x N underlying layer. Science China: Physics, Mechanics and Astronomy, 2010, 53, 445-448.	5.1	1
43	The influence of pressure on the growth of a-plane GaN on r-plane sapphire substrates by MOCVD. Science China: Physics, Mechanics and Astronomy, 2011, 54, 446-449.	5.1	1
44	The photocurrent of resonant tunneling diode controlled by the charging effects of quantum dots. , 2012, , .		1
45	Low-Dimensional Semiconductor Structures for Optoelectronic Applications. Advances in Condensed Matter Physics, 2015, 2015, 1-2.	1.1	1
46	A novel method to reduce the period limitation in laser interference lithography. Optical and Quantum Electronics, 2015, 47, 2331-2338.	3.3	1
47	Influence of Sb ₂ soaking on strained InAs _{0.8} Sb _{0.2} /Al _{0.2} Ga _{0.8} Sb multiple quantum well interfaces. AIP Advances, 2021, 11, 075004.	1.3	1
48	Improving the Performance of Solar Cells Under Non-Perpendicular Incidence by Photonic Crystal. IEEE Photonics Journal, 2021, 13, 1-4.	2.0	1
49	Ag/Si multilayers with nanometer sized particles of silver during annealing process. Science in China Series A: Mathematics, 1998, 41, 989-994.	0.5	0
50	MBE growth of high absorption mid-IR type-II InAs/GaSb superlattices. Science Bulletin, 2014, 59, 2383-2386.	1.7	0
51	Efficiency enhancement of InGa _x N/GaN multiple quantum wells with graphene layer. Applied Physics A: Materials Science and Processing, 2015, 119, 1209-1213.	2.3	0
52	Monolithic light emitting device and light detecting device fabricated with a commercial LED wafer. Optical and Quantum Electronics, 2020, 52, 1.	3.3	0